

Organic Superconductors (Springer Series in Solid State Sciences, Vol 88)

by T Ishiguro and K Yamaji

Springer-Verlag : Berlin-Heidelberg-New York-London-Paris-Tokyo-Hong Kong, 1990
x+288 pages, 189 figures ; price: DM 99 (Hard cover) ; ISBN 3-540-51321-3

“Organic Superconductors” by T Ishiguro and K Yamaji is a recent publication in the well-known “Springer Series in Solid State Sciences”.

The authors are involved, along with their colleagues at the Kyoto University and the Electrotechnical Laboratory, Ibaraki, in pioneering research on superconductivity and other related physical properties of organic materials. The present book is an introduction to these topics and more importantly, a review of the current (up to 1989 end) status. Naturally, the authors' experience has led to a balanced and clearly written coverage of the physics of organic conductors and superconductors.

While most of the organic materials are electrical insulators, there are three types of organic conductors - charge transfer compounds (like the Bechgaard salts), intercalated graphite and doped polymers. Except a discussion in the last section on the difficulties and the possibility of a polymer-based superconductor, the book deals with the first type of organic conductors, namely the charge transfer salts, some of which exhibit superconductivity.

In $(\text{TMTSF})_2\text{X}$ or Bechgaard salt (1978) type organic superconductors, electrons have been transferred from TMTSF-groups to groups denoted by X. Each set of groups is so stacked in the 3-D structure that there are cation columns and anions columns. Obviously electrical conduction along the columns is high making these crystals primarily 1-D in character. But some inter-columnar or transverse conductivity is needed to achieve superconductivity. In fact these salts have quasi 1-D character, and $(\text{BEDT-TTF})_2\text{X}$ type salts (1988) have quasi 2-D characters.

For quasi 1-D conductors, following ground states are expected to occur : CDW or charge density wave, SDW or spin density wave, singlet superconductivity and triplet superconductivity, under different conditions. The tests of such theories through observations on suitable organic conductors have been given the deserved coverage in the book.

Chapter 1 is an introduction to the subject listing basic data on all the 34 organic superconductors discovered before nineties. Structures of their principal molecular complexes are also given. For example, ET stands for BEDT-TTF or bis-ethylenedithia-tetrathiafulvalene, and its organic structure is given.

Fundamentals of conduction in organic materials are briefly discussed in Chapter 2. The electrons in π -orbitals in these materials are delocalized and important for conduction allowing π -electron approximation. Further simplifica-

tions and a molecular orbital method are then adopted to outline the quantum mechanical calculation of the electronic states of charge transfer salts. Peierls Transition, Froehlich Conduction, CDW and the Open Fermi surface are shown to arise from the quasi one dimensional character. The effect of additionally considering the Coulomb repulsion in above calculations is also discussed in light of some NMR, susceptibility and diffuse X-ray scattering observations.

Chapter 3 is on $(\text{TMTSF})_2\text{X}$ where S stands for Se, and $(\text{TMTTF})_2\text{X}$ containing sulphur atoms instead of Se. Their crystal and electronic structures, the anisotropic electrical conduction, and possible transition on cooling from a metallic to an insulating SDW phase preventing appearance of superconductivity are reviewed. It is shown that either a mechanical pressure or a suitable chemical substitution may suppress the appearance of the SDW ordering and thus allow a superconducting phase. It is discussed that although specific heat jump at T_c and the energy gap deduced from tunneling are consistent with the BCS theory, the dynamic aspects of electron conduction as probed by nuclear relaxation rate measurement are unlike the BCS superconductors.

Chapter 4 explains theoretically our understanding of the SDW phase and also the possibility of reentrant superconducting phases. Capability of the 1-D electron gas theory or g-ology is first explored. Observations related to SDW are finally shown to be reproduced fairly well by the mean field treatment on basis of an anisotropic 2-D tight binding band model.

Near 10 K superconductors of the $(\text{ET})_m\text{X}_n$ family where ET represents BEDT-TTF compound are discussed in Chapter 5. Above-mentioned properties are described here for these ET compounds, many of which have the added attraction of having quasi two dimensional character. Structural phase transformations of ET salts on tempering have been covered. The then highest T_c organic superconductor, for example, is $(\text{ET})_2\text{Cu}(\text{NCS})_2$ in kappa phase. Special ET-superconductors like $(\text{ET}_2)\text{ReO}_4$ are also outlined.

Chapter 6 is on DMET and MDT-TTF superconductors. DMET is a hybrid between TMTSF and ET molecular groups and hence interesting. Superconductivity in MDT-TTF is more interesting as it is a cross between two apparently non-superconducting groups TTF and BMDT-TTF. Chapter 1 is on DHIT salts. These superconductors are π -anion molecules while the earlier ones have been π -cation molecules.

The mechanism of superconductivity in organic materials, which is yet to be decided from among a few possible mechanisms, is expertly documented in Chapter 8. Outline of BCS theory, s-, p-, d- pairings and singlet and triplet superconductivity are given with notes on Little's models of 1964 and 1983. Next the possibility of superconductivity from spin fluctuations in $(\text{TMTSF})_2\text{X}$, for example, is reviewed. That this mechanism is hotly debated for explaining high T_c superconductivity has also been noted by the authors. They next explain

another mechanism in which electron-molecular-vibration interaction in the skeleton of TTF-derived superconductors provide electron-photon coupling. Calculation of T_c based on such an idea is indicated. The results of point contact tunneling experiment, and their analysis in the framework of strong coupling theory is discussed in the next section. Other theories like g-ology, excitonic, bipolaron and 2-band mechanisms as well as theories of possible superconductivity in polymers have been outlined very briefly but in clear terms.

Chapter 9 is on a new phenomenon first observed around 1981 in organic superconductors. That is the magnetic field induced spin density wave or FI-SDW. Various experimental observations as well as Gor'dov-Lebed' and Green's function theories have been covered.

Chapter 10, shortest in the book, is on prospects of new developments. The discussion on relation (of organic superconductors) to high- T_c oxide superconductors and the note on possible new organic superconductors are refreshing.

In the preface the authors write: "Because we are not expert in the areas, chemical synthesis and crystal growth are not discussed". In spite of this declaration by the authors, any reader of the book would like to learn from the same authors in the same book an outline of the preparation processes of these exciting organic compounds, only briefly mentioned in some of the original papers. In future, if an expanded edition is published to include post-1989 developments, a chapter on chemical synthesis and crystal growth may be tried.

The compilation of references is sufficiently careful and complete to let a beginner depend on this compilation alone. But the success of the book lies in explaining most of the topics in the coherent write-up of the book itself, without any frequent need to read references. So the book is recommended not only to researchers but also to all university libraries. It really fills a gap, uncovered by any earlier book.

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Amorphous and Crystalline Silicon Carbide II: Recent Developments
(Springer Proceedings in Physics, Vol 43)

(Proceedings of the 2nd International Conference, Santa Clara, California, Dec, 15-16, 1988)

edited by M M Rahman, C Y-W Yang and G L Harris

Springer-Verlag: Berlin-Heidelberg-New York-London-Paris-Tokyo-Hong Kong, 1989

x+232 pages, 197 figures; price: DM 90 (Hard cover); ISBN 3-540-51656-5

This book serves a very useful purpose—that of bringing upto date the latest developments in a field which tends to get segregated by the diversity of applications. Silicon carbide is a semiconductor of considerable importance in both its

cubic-crystalline form and its hydrogenated amorphous form although the relevant preparation processes are quite different. The book is divided into six parts: the first two parts are dedicated to the growth, the third part to the characterization of bulk properties and the fifth to the interfaces, the fourth part deals briefly with diamond thin films and its applications, the sixth and final part covers the preparation and the characteristics of the devices.

Part I

Of the eight papers in this section, the first four are dedicated to thermal CVD of cubic silicon carbide. This method is known to produce high quality material and is demonstrated here, evidenced by a range of characterization techniques. The fifth paper (Nakata *et al*) shows that the vacuum sublimation method can yield sufficiently good quality material to enable fabrication of blue light emitting diodes. The change of SiC polytype from 3C to 6H during high temperature anneal has been reported in the sixth paper (Yoo *et al*). The abstracts of paper six and seven of part one introduce the effects of alloying SiC with germanium in films grown by radio frequency sputtering and the one dimensional modelling of CVD growth of SiC. The first of the efforts tend to open up a new region of materials and the second at giving a quantitative picture is very useful.

Part II

In this section the preparation of amorphous and microcrystalline SiC by the RF glow discharge technique or its modification—the controlled plasma magnetron technique is the subject of the first three papers. The interest of these papers however lies in the possibility of easy device fabrication. This is a fast emerging area and is receiving the deserved attention. The fourth paper is an effort to analyze the effect of depositing carbon onto silicon substrates by ECR decomposition of methane/hydrogen mixture. The last paper in this section reports the preparation of a-SiC by dipping in polycarbosilane followed by annealing in argon ambient. This method yields material that is different from the one prepared by plasma decomposition and comparison is presented.

Part III

The first four papers in this section presents results of characterization of amorphous silicon carbide. The first paper deals with gap state spectroscopy and mobility determination from the time of flight method. The next three papers deal with structural studies with photo electron spectroscopy, infrared absorption spectroscopy and small angle x-ray scattering spectroscopy. These works correlate increasing structural disorder with alloying and changes in the type of bonding. The fifth paper (Okumura *et al*) reveals recombination centers in 3C-SiC by ICTS and correlates this with hall mobilities. The following paper presents an ESR study of the same material while the seventh presents its photoluminescence study. The ESR spectra is shown to consist of these lines below 40K. This interpreted as

being due to a broad line and a superfine pair whose temperature dependences suggest that they arise from independent paramagnetic centres. An irradiation induced (MeV electrons) defect is also identified and its annealing behaviour established. The TR photo luminescence data corroborate the existence of a deep donor in undoped *n*-type SiC that is observed in temperature dependence hall mobility measurements. The subsequent paper is from the same group and shows how luminescence imaging can be interpreted to yield partial distribution of recombination centers. The mechanism of formation of stress induced defects in CVD-SiC is discussed in the next abstract. The following paper (Nordquist *et al*) presents a study of antiphase boundaries as revealed by an eutectic etch which is carried out at a lower temperature. A variation in density of antiphase boundaries with process parameters in the CVD process is established. The following abstract claims to use ellipsometric studies at different angles to get absolute values of refractive index and extinction coefficient of cubic-SiC. These results are supposed to show that the CVD films contain 30-40 vol % of amorphous silicon. The following abstract reports the growth induced defects in epitaxial cubic SiC grown on different Si surfaces orientation as revealed by photo luminescence and TEM. The subsequent abstract correlates vibrational infrared absorbing modes in *a*-SiC : H with their electrical properties in undoped and doped material.

Part IV

The first (invited ?) paper makes a case for the use of thin film diamond based on its superior properties for several application. The discussion terminates on a note lamenting the lack of success of hydrogen ambient techniques due to the strength of the C-H bonding. The next paper discusses material requirements for high power electronic devices and concludes that wide gap materials like SiC and diamond are superior. The final abstract of this part discusses some active material and possible material application of CVD diamond films.

Part V

The first paper in the section analyses the all important Si (100)/3C-SiC interfaces using a triad - MEIS, SXS and TEM. The conclusions are quite important that the buffer layer is almost completely 3C-SiC with only a few nm thick distorted region at the interface - which is the real buffer layer. The next abstract promises to examine the role of hydrogen in the growth of crystalline phase in plasma deposition of thin film semiconducting materials at low temperatures. The following paper presents a study of *a*-SiC/C-Si interface using high resolution transmission electron microscopy. This study reveals that such a heterostructure form an abrupt, uncontaminated interface. The subsequent paper presents the results of efforts to grow cubic SiC by gas source MBE at 1000°C on a cubic SiC substrate grown on CSi by CVD. SHEED Patterns reveals good crystalline growth. The final abstract in this part reports the formation of a Cr contact on SiC.

Part VI

The first paper in this part discusses the preparation of amorphous silicon carbide and microcrystalline silicon carbide followed by their application as window layer of solar cells, semitransparent solar cells, electrophotography and light emitting diodes. The next paper discusses problems in growth of epitaxial β -SiC on TiC_x substrates as revealed by characteristics of Schottky diodes. The fabrication of β -SiC FET is also demonstrated. The next paper discusses the fabrication of β -SiC MOSFETs and its performance from RT to 500°C. The next paper discusses the fabrication and performance of β -SiC buried gate JFET. A different structure is reported – the channel β -SiC (*n* type) is grown on a *p*-type α -SiC substrate which it is claimed, reduces the junction defect density. However, the claim that a 3- μm thick interface defect layer is formed has been negated in another paper in this book (Iwami *et al*). The next paper describes a different application – as a gate insulation via GaAs FET. A fit of experimental frequency dependent conductance measurements with their model shows that SiC is not sufficiently insulating to serve as insulator in a GaAs MISFET. When prepared by plasma, triode dc sputtering. The subsequent paper presents several applications of free standing SiC films prepared by CVD on graphite. The methods to remove the substrate and the details of processing for use of the SiC films in several practical mechanical applications are described. The subsequent paper presents the characteristics of Si/SiC heterojunction bipolar transistors in which the β -SiC is grown by electron beam evaporation at substrate temperature below 1000°C and shown to have a polycrystalline structure. The common emitter gain of the HBT is about 2.5 and is explained as being due to a defective interface region. The following paper reports on TFTs prepared by the same technique. In this case the hall mobility is comparable to that in the previous paper but the field effect mobility ($37 \times 10^{-5} \text{ cm}^2/\text{Vs}$) is rather low compared to CVD SiC. The subsequent paper addresses an important aspect of semiconductor device processing – etching. The mechanisms of SiF_6/O_2 , CHF_3/O_2 and $\text{CB}_r\text{F}_3/\text{O}_2$ etching system are reported. The SiC etch rate is found to be determined by chemical mechanisms at DC bias below –300V and is lower than Si by an order of magnitude and comparable to that of SiO_2 , etch rate.

The tungsten-SiC contact is investigated in the next paper and shown to be ohmic. The last abstract introduces the idea of XeCl, eximer laser processing for doping of SiC.

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Semiconductor Silicon : Materials Science and Technology (Springer Series in Materials Science, Vol 13)

(Proceedings of the Summer School Erice, Trapani, Sicily, July 3-15, 1988)

edited by G Harbeke and M J Schulz

Springer-Verlag : Berlin-Heidelberg-New York-London-Paris-Tokyo-Hong Kong, 1989
ix + 345 pages, 260 figures ; price : DM 104 (Hard cover) ; ISBN 3-540-51073-7

The book "Semiconductor Silicon" is a compilation of the lectures delivered at the Summer School at Erice, Sicily during July 3-15, 1988. The topics of the lectures include various aspects of silicon, which are of high importance. During the last decade, the rapid progress of the semiconductor technology and the inflation of cheap memory capacity have resulted in the revolution in the micro-electronics and related industries. For example, the evolution of the mainframe computers, workstations, personal computers have been possible due to these rapid developments of semiconductor memories. An ideal semiconductor memory should have a high density, low power dissipation, random access alongwith a high performance and reliability. Although no single device, satisfying all these requirements have been achieved in practice, a thousandfold increase in the intergration density has resulted in the miniaturization of chip sizes to less than submicron. Due to this immense scientific progress in a very short time, the silicon technology has become very complex. As a result, precise control over the electrical, optical and mechanical properties have become necessary during the fabrication of various important silicon based devices. The present book will surely be of great help towards the understanding of the above, through the consideration of different aspects of Si alongwith its processing for device applications.

The lectures included in the book disseminate the experiences of several internationally reputed experts in the field of semiconductors. Starting from the basic crystal growth technique (part I), the processing and defects have been discussed in the subsequent parts.

Characterisation of materials is considered to be the most important aspect in the semiconductor device applications. Different techniques of characterisation including non-destructive ones have been dealt with great care in the part IV and in the subsequent parts which include the various aspects of transient spectroscopy and optical characterisation. Inclusion of high resolution electron microscopy and tunneling microscopy alongwith surface analysis as methods to investigate defects in semiconductors, has made the book indispensable to the scientists working on Si.

Discussions related to the insulating films have been dealt with, in the part V. Extension of the characterisation technique to the studies of Si-SiO₂ interfaces is very useful. Si-SiO₂ interface is of high importance in metal oxide semiconductor

(MOS) devices in which SiO_2 is used for the surface passivation and as the gate dielectric for Si MOSFET. Although Si– SiO_2 interfaces have been extensively studied in the past, the properties of interfaces are not well understood till now. The discussions on the characterisation of Si– SiO_2 interfaces will be of immense help in understanding the physical and chemical properties of the interfaces which are directly linked to the progress in Si MOS technology. A recent device design based on a trench cell capacitor along with its reliability problems have been presented in part VII.

As silicides are required in the VLSI processes, properties of the silicide films including the morphology and structure of thin TiSi_2 films on silicon and also the modelling of the diffusion phenomena in silicides are of high importance. These aspects of the silicon technology have been discussed extensively in part VI. An excellent review on the main developments during the last decade in this field of electronic characterisation of the bulk silicides and their theoretical description has also been included. A valuable discussion on the device application related to these aspects have been included in part VII.

It should be mentioned that the editors have taken great care in compiling the lectures mentioned above, for which they deserve heartfelt thanks from the readers. I am sure that the way of presentation of the lectures will appear to be very comprehensive to the researchers working on Si and related areas. I have no hesitation to say that this book will be of immense help to the semiconductor device technologists and researchers.

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Electronic Properties of Conjugated Polymers III, Basic Models and Applications (Springer Series in Solid State Sciences, Vol 91)

(Proceedings of an International Winter School, Kirchberg, Tirol, March 11-18, 1989)

edited by H Kuzmany, M Mehring and S Roth

Springer-Verlag : Berlin-Heidelberg-New York-London-Paris-Tokyo, Hong Kong, 1989
xiv+484 pages, 251 figures ; price : DM 110 (Hard cover) ; ISBN 3-540-51319-1

In recent years, the applications of polymers have diversified in several newer directions such as nonlinear optics, molecular electronics and so on. In tune with this, there has been a very wide-spread interest in the study of polymers. The present volume which is the outcome of an International Winter School held from March 11-18, 1989, in Kirchberg (Austria), gives some of the more recent perspec-

tives of the research in conjugated polymers. It contains over eighty articles which are subdivided in thirteen sections.

Although it is not possible to discuss all the articles, it is worthwhile to mention the title of the thirteen sections to give an overall idea of the contents. The thirteen sections are respectively, on transport properties and structure of polymers, theory, optical excitation, IR and Raman spectroscopy, electrochemistry of polyanilines, magnetic resonance, nonlinear optics, molecular electronics, properties of polyaniline, polythiophenes and oligoenes, high temperature superconductors and lastly applications of polymers. Though most of the articles report original research, a few (e.g. those on high- T_c superconductors) were tutorial type which will be appreciated more by the beginners.

A number of polymeric materials e.g. polyanilines, polythiophenes, polyacetylene and their potential applications in semiconductor devices and bioelectronics devices have been described.

The transport properties of polymers and in excited electronic states continue to be an active field. The more recent developments is the nonlinear optical properties of these polymers. The general consensus which emerges is that the most important factors are the conjugation length and disorder.

While an wide assortment of optical and electron spectroscopy has been applied on the experimental side, a variety of theoretical models ranging from polaron, soliton to quantum chemical methods have been employed to elucidate the structure, conductivity and non-linear optical properties of polymers.

This volume is bound to evoke a lot of interest to a rather wide audience ranging from polymer-electrochemist to solid state physicists on one hand from electrical engineers to biochemists on the other. Thus, this volume is going to be very important and useful addition to all science and engineering libraries.

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Photoacoustic, Photothermal and Photochemical Processes at Surfaces and in Thin films (Topics in Current Physics, Vol 47)

edited by P Hess

Springer-Verlag : Berlin-Heidelberg-New York-London-Paris-Tokyo-Hong Kong, 1989

xiv + 376 pages, 234 figures ; price ; DM 109 (Hard cover) ; ISBN 3-540-51703-0

This book reviews the advancements made in the areas of photoacoustic, photothermal and photochemical processes in recent times. Besides dealing with the instrumentation associated with the studies of the above processes in thin films

and surfaces in detail, this book presents a precise description of the mechanisms involved in laser-induced desorption, ablation and surface damage, depth profiling, nondestructive techniques for testing, the analysis of thin films and interfaces by using thermal and acoustic waves, surface acoustic waves and magnetic resonance in ferromagnetic films. All the above topics including an introductory chapter are delineated in twelve chapters. The introductory chapter by Professor Hess (editor) presents a lucid description of the characteristic features of the processes involving photoacoustic, photothermal and photochemical phenomena.

In subsequent chapters, details of specific processes were discussed by different experts in the respective fields. Some of them needs special mention.

Studies on the laser-induced desorption stimulated by electronic excitation is of current interest and predicts the possibilities of other exciting processes. The above has been discussed in detail by Trager by elaborating the existing theoretical description of the process. He has very carefully indicated the inadequacy of the present state of understanding of the above process and suggested the need of motivated experiments to be performed with accurate control of experimental parameters like variation of the excitation wave length, angle of incidence and the polarization. Modern experimental techniques were also taken up in this chapter with an indication of the need of ultrafast light pulses which will provide information on nonequilibrium processes.

The other chapter, needs mention, is by Matthais and Dreyfus on thermal and non-thermal effects in laser-surface interaction on metallic and wide bandgap ionic materials. Individual particle emission to ablation and surface damage phenomena were dealt in detail with requisite description of the basic principles of the experiments alongwith appropriate data interpretation. Other chapters on photothermal analysis of thin films, locally resolved magnetic resonance in ferromagnetic layers and films are also selfcontained and instructive.

Thus, this book presents a decent and useful overview of the recent advancement and developments in the areas of photoacoustic, photothermal and photochemical processes in surfaces and thin films. The reviewer has no hesitation to say that this book will be extremely useful as a reference book to the scientists working in the areas of thin films and surfaces.

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We will be publishing a short introduction to the Books we receive from Publishers. The detailed *Review* will be published in due course in our regular Book Review Section—Ed.

Direct and Inverse Problems : Potentials in Quantum Scattering

by B N Zakhariev and A A Suzko

(Translated from the Russian by G Pontecorvo)

Springer-Verlag, 1990, 3-540-52484-3

xiii + 223 pages, 42 figures, Soft cover, DM 48.00

This book is mainly divided into two parts. The part I is devoted to one-dimensional, one-channel system whereas the part II is to multichannel, multi-dimensional, multi-particle problems. In part I there are four chapters viz the Principal equations of scattering theory, exactly solvable models : Bargmann potentials V^B , approximate solutions, and the Levinson theorem. In part II there are three chapters, multi-channel equations, multi-dimensional problems and multi-particle systems. At the end of each chapter an article 'notes on the literature' is given and there are also few exercises left for the readers.

K Roy

Variational Methods (Progress in Nonlinear Differential Equations and Their Applications, Vol. 4)

edited by H Berestycki, J M Coron and I Ekeland

Birkhauser, 1990, 3-7643-3452-5

ix + 478 pages, 13 figures, Hard cover, SFR 98.00

The book is the proceedings of a Conference (on the special nonlinear year) held in Paris, June 1988. Over the last few decades the methods of nonlinear analysis have found a wide range of applicability in physical science, e.g. in the study of Hamiltonian systems in mechanics, in the mathematical theory of liquid crystals, in geometry, in relativity, in partial differential equations and in mathematical physics. The application of variational methods to some of these and related problems has been the focal theme of the book. The book is primarily designed for mathematicians and mathematical physicists.

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Chemistry and Physics of Solid Surfaces-VIII (Springer Series in Surface Sciences, Vol. 22)

edited by R Vanselow and R Howe

Springer-Verlag, 1990, 3-540-52679-x

xv + 464 pages, 234 figures, Hard cover, DM 138.00

This book with 18 chapters contains selected review articles presented at the 9th International Summer Institute in Surface Science (1989). The articles cover mechanisms for activation and desorption of molecules at the surfaces, photo-